

Molding Type Module IGBT 2-in 1-Package, 1200 V, 75 A


INT-A-PAK

FEATURES

- High short circuit capability, self limiting to 6 x I_C
- 10 µs short circuit capability
- V_{CE(on)} with positive temperature coefficient
- Low inductance case
- Fast and soft reverse recovery antiparallel FWD
- Isolated copper baseplate using DCB (Direct Copper Bonding) technology
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

PRIMARY CHARACTERISTICS

V _{CES}	1200 V
I _C at T _C = 80 °C	75 A
V _{CE(on)} (typical) at I _C = 75 A, T _J = 25 °C	1.90 V
Speed	8 kHz to 30 kHz
Package	INT-A-PAK
Circuit configuration	Half bridge

TYPICAL APPLICATIONS

- AC inverter drivers
- Electronic welders
- Switching mode power supplies

DESCRIPTION

Vishay's IGBT power module provides ultra low conduction loss as well as short circuit ruggedness. It is designed for applications such as general inverters and UPS.

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V _{CES}		1200	V
Gate to emitter voltage	V _{GES}		± 20	
Collector current	I _C	T _C = 25 °C	150	A
		T _C = 80 °C	75	
Pulsed collector current	I _{CM} ⁽¹⁾	t _p = 1 ms	150	
Diode continuous forward current	I _F	T _C = 80 °C	75	
Diode maximum forward current	I _{FM} ⁽¹⁾	t _p = 1 ms	150	
Maximum power dissipation	P _D	T _J = 150 °C	543	W
Short circuit withstand time	T _{SC}	T _J = 125 °C	10	µs
I ² t-value, diode		V _R = 0 V, t = 10 ms, T _J = 125 °C	1050	A ² s
RMS isolation voltage	V _{ISOL}	f = 50 Hz, t = 1 min	2500	V
Maximum junction temperature	T _J		+150	°C

Note

⁽¹⁾ Repetitive rating: pulse width limited by maximum junction temperature

IGBT ELECTRICAL SPECIFICATIONS (T_C = 25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	V _{(BR)CES}	V _{GE} = 0 V, I _C = 1.0 mA, T _J = 25 °C	1200	-	-	V
Collector to emitter voltage	V _{CE(on)}	V _{GE} = 15 V, I _C = 75 A, T _J = 25 °C	-	1.9	2.35	
		V _{GE} = 15 V, I _C = 75 A, T _J = 125 °C	-	2.1	-	
Gate to emitter threshold voltage	V _{GE(th)}	V _{CE} = V _{GE} , I _C = 3.0 mA, T _J = 25 °C	5.0	6.2	7.0	
Collector cut-off current	I _{CES}	V _{CE} = V _{CES} , V _{GE} = 0 V, T _J = 25 °C	-	-	5.0	mA
Gate to emitter leakage current	I _{GES}	V _{GE} = V _{GES} , V _{CE} = 0 V, T _J = 25 °C	-	-	400	nA

**SWITCHING CHARACTERISTICS**

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 600\text{ V}$, $I_C = 75\text{ A}$, $R_g = 10\ \Omega$, $V_{GE} = \pm 15\text{ V}$, $T_J = 25\text{ }^\circ\text{C}$	-	305	-	ns
Rise time	t_r		-	67	-	
Turn-off delay time	$t_{d(off)}$		-	328	-	
Fall time	t_f		-	187	-	
Turn-on switching loss	E_{on}		-	6.74	-	mJ
Turn-off switching loss	E_{off}		-	4.25	-	
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 600\text{ V}$, $I_C = 75\text{ A}$, $R_g = 10\ \Omega$, $V_{GE} = \pm 15\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$	-	311	-	ns
Rise time	t_r		-	67	-	
Turn-off delay time	$t_{d(off)}$		-	347	-	
Fall time	t_f		-	337	-	
Turn-on switching loss	E_{on}		-	9.75	-	mJ
Turn-off switching loss	E_{off}		-	7.05	-	
Input capacitance	C_{ies}	$V_{GE} = 0\text{ V}$, $V_{CE} = 25\text{ V}$, $f = 1.0\text{ MHz}$, $T_J = 25\text{ }^\circ\text{C}$	-	5.52	-	nF
Output capacitance	C_{oes}		-	0.40	-	
Reverse transfer capacitance	C_{res}		-	0.26	-	
SC data	I_{SC}	$t_s \leq 10\ \mu\text{s}$, $V_{GE} = 15\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$, $V_{CC} = 900\text{ V}$, $V_{CEM} \leq 1200\text{ V}$	-	350	-	A
Internal gate resistance	R_{GINT}		-	3	-	Ω
Stray inductance	L_{CE}		-	-	30	nH
Module lead resistance, terminal to chip	$R_{CC'+EE'}$		-	0.75	-	m Ω

DIODE ELECTRICAL SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Forward voltage	V _F	I _F = 75 A	T _J = 25 °C	-	1.78	2.18	V
			T _J = 125 °C	-	1.85	-	
Reverse recovery charge	Q _{rr}	I _F = 75 A, V _R = 600 V, dI _F /dt = 1300 A/μs V _{GE} = -15 V	T _J = 25 °C	-	4.0	-	μC
	T _J = 125 °C		-	9.3	-		
Peak reverse recovery current	I _{rr}		T _J = 25 °C	-	55	-	A
			T _J = 125 °C	-	73	-	
Reverse recovery energy	E _{rec}		T _J = 25 °C	-	2.98	-	mJ
			T _J = 125 °C	-	4.46	-	

THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction temperature	T _J		-	-	150	°C
Storage temperature range	T _{Stg}		-40	-	125	°C
Junction to case per ½ module	R _{thJC}	IGBT	-	-	0.23	K/W
		Diode	-	-	0.33	
Case to sink (conductive grease applied)	R _{thCS}		-	0.05	-	
Mounting torque		Power terminal screw: M5	2.5 to 5.0			Nm
		Mounting screw: M6	3.0 to 5.0			
Weight		Weight of module	-	150	-	g

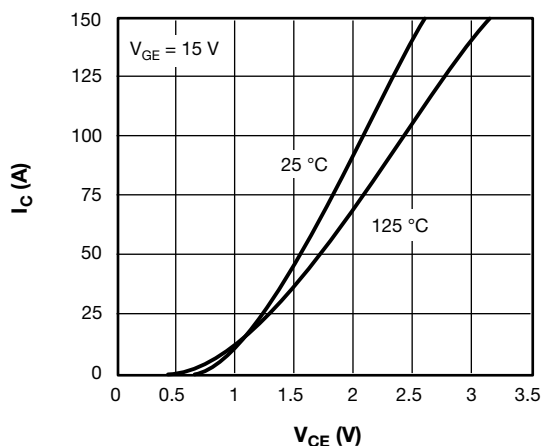


Fig. 1 - IGBT Typical Output Characteristics

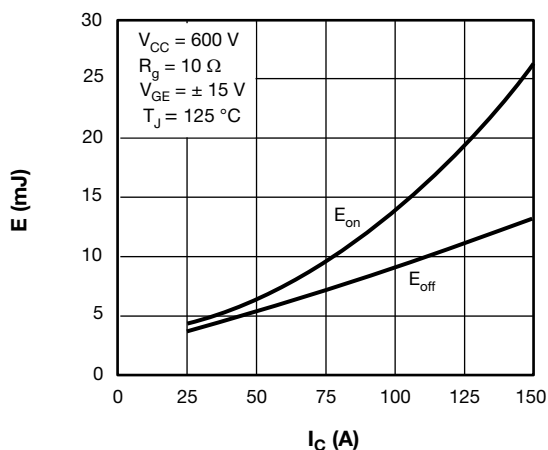


Fig. 3 - IGBT Switching Loss vs. I_C

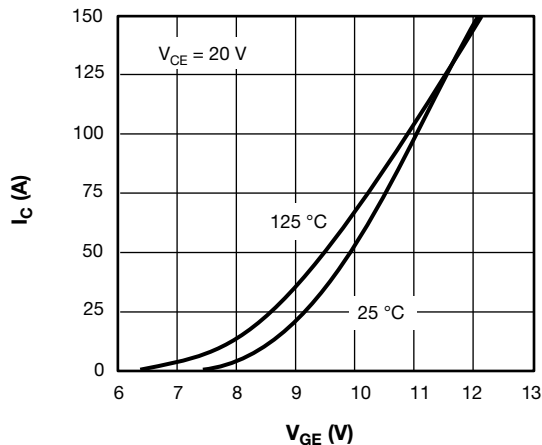


Fig. 2 - IGBT Typical Transfer Characteristics

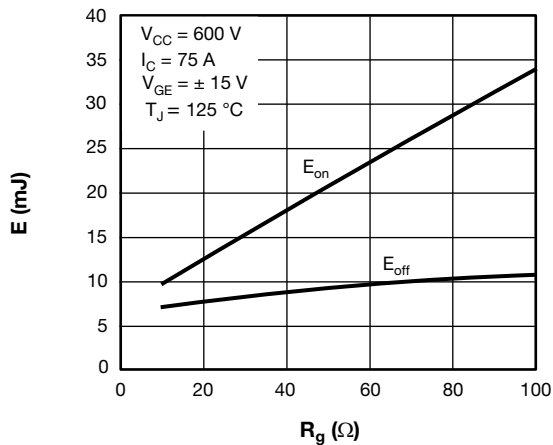


Fig. 4 - IGBT Switching Loss vs. R_g

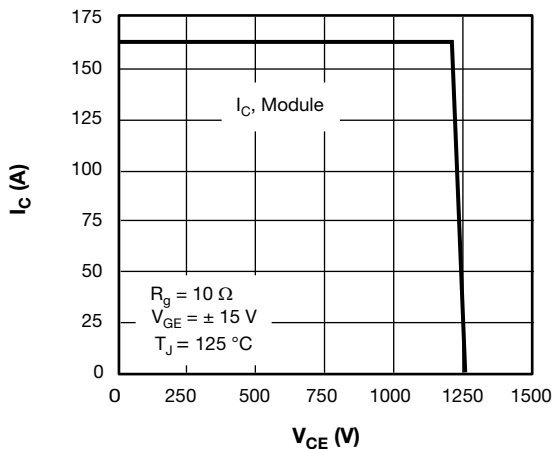


Fig. 5 - RBSOA

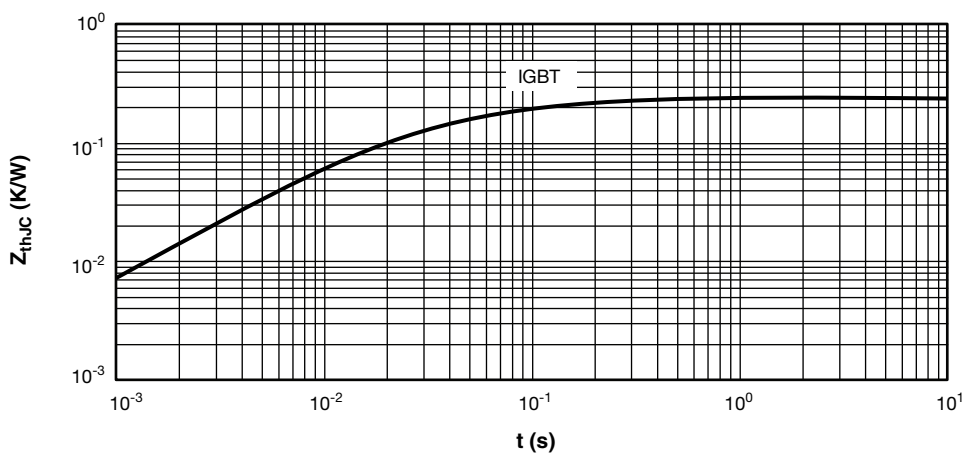


Fig. 6 - IGBT Transient Thermal Impedance

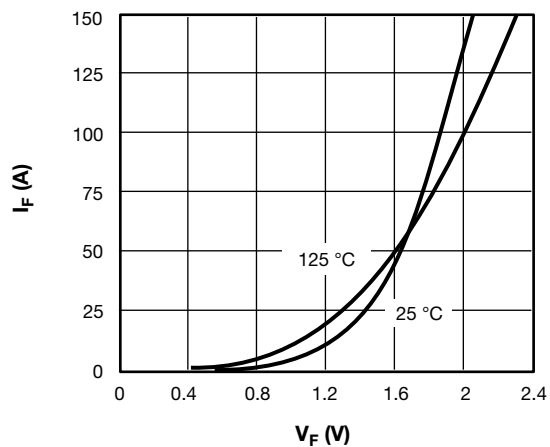


Fig. 7 - Typical Diode Forward Characteristics

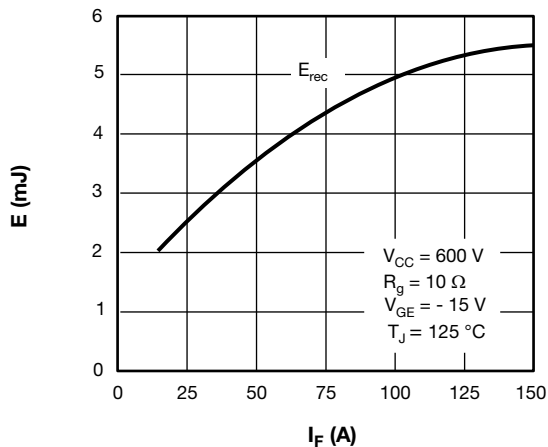


Fig. 8 - Diode Switching Loss vs. I_F

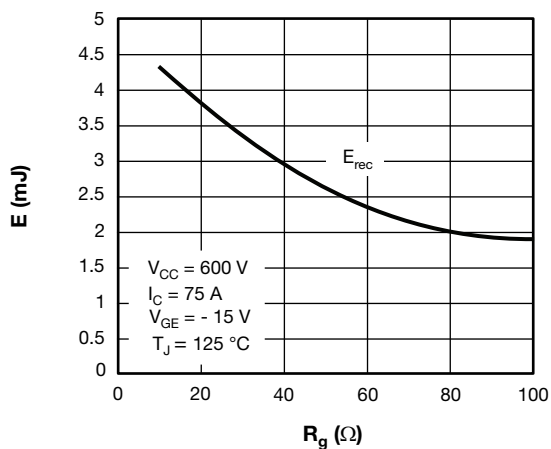


Fig. 9 - Diode Switching Loss vs. R_g

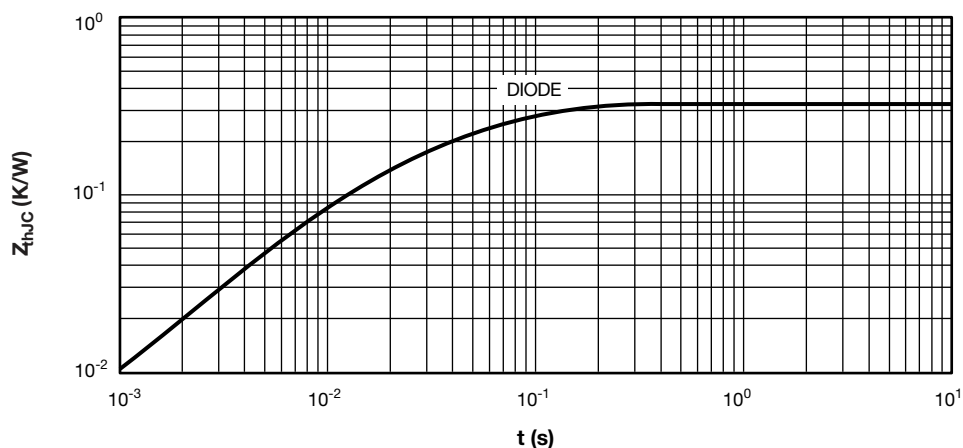
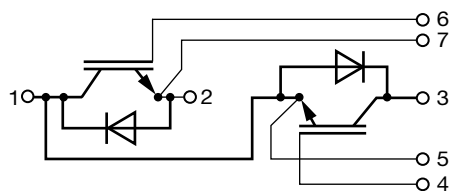


Fig. 10 - Diode Transient Thermal Impedance

CIRCUIT CONFIGURATION

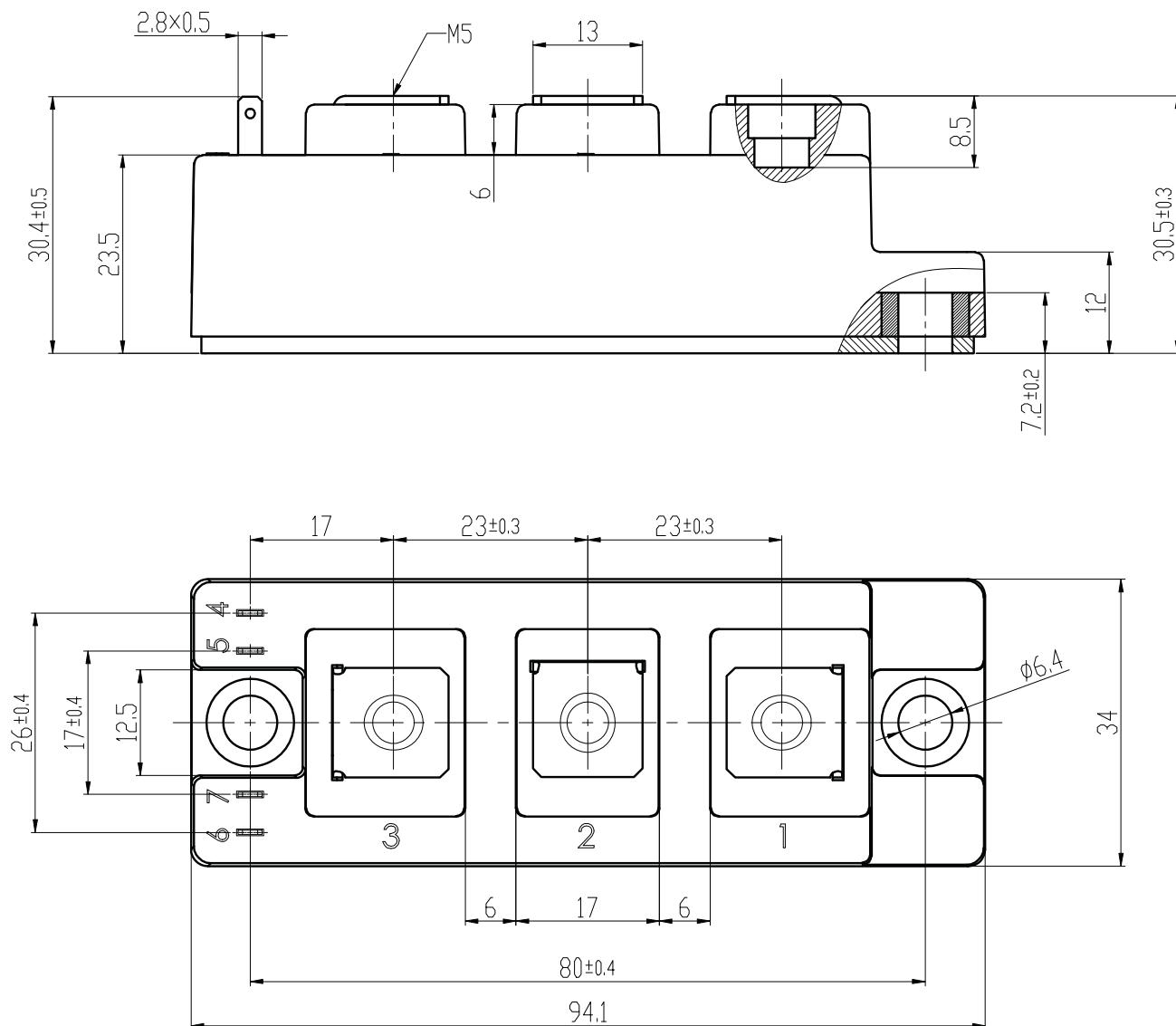


LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95524



INT-A-PAK

DIMENSIONS in millimeters (inches)





Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.